



# 8N60K-MT

**Power MOSFET**

## 8A, 600V N-CHANNEL POWER MOSFET

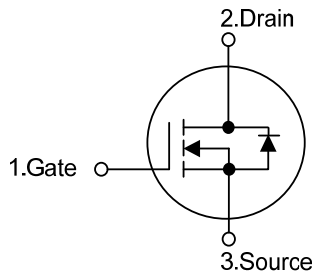
■ DESCRIPTION

The UTC **8N60K-MT** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

- \*  $R_{DS(ON)} < 1.2\Omega$  @  $V_{GS} = 10V, I_D = 4.0A$
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

■ SYMBOL

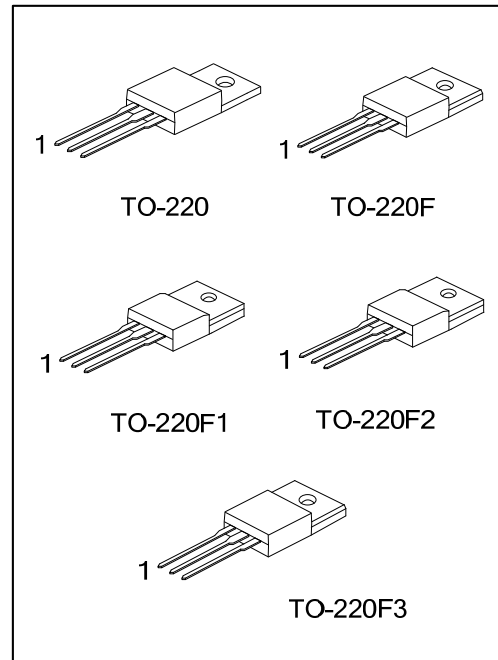


■ ORDERING INFORMATION

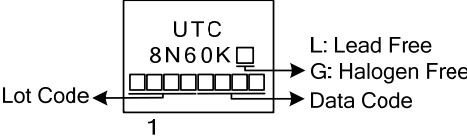
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N60KL-TA3-T	8N60KG-TA3-T	TO-220	G	D	S	Tube
8N60KL-TF1-T	8N60KG-TF1-T	TO-220F1	G	D	S	Tube
8N60KL-TF2-T	8N60KG-TF2-T	TO-220F2	G	D	S	Tube
8N60KL-TF3-T	8N60KG-TF3-T	TO-220F	G	D	S	Tube
8N60KL-TF3T-T	8N60KG-TF3T-T	TO-220F3	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8N60KL-TF1-T</p>	<p>(1) T: Tube                  (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2                  TF3: TO-220F, TF3T: TO-220F3                  (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	600	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	8	A
	Pulsed (Note 2)	$I_{DM}$	32	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	365	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	$P_D$	147	W
	TO-220F/TO-220F1		48	W
	TO-220F2/TO-220F3			
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Operating Temperature		$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by  $T_J$ .

3.  $L = 11.4\text{mH}$ ,  $I_{AS} = 8\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$ .

4.  $I_{SD} \leq 7.5\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$ .

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	$\theta_{JC}$	0.85	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$
	TO-220F2/TO-220F3			

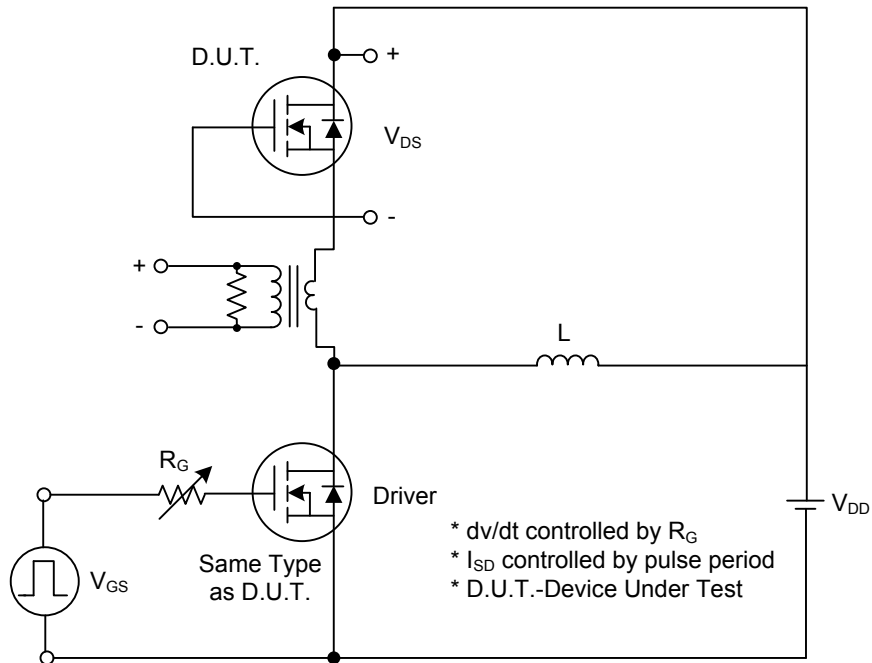
■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	600			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>			100	nA
	Reverse				V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0V	-100
Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA, Referenced to 25°C		0.7		V/°C
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.0A			1.2	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz		1120	1255	pF
Output Capacitance	C <sub>OSS</sub>		120	135	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>		13	16	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	Q <sub>G</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =1.0V, I <sub>D</sub> =1.3A (Note 1, 2)		28	36	nC
Gate-Source Charge	Q <sub>GS</sub>		8		nC	
Gate-Drain Charge	Q <sub>GD</sub>		6		nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.5A, R <sub>G</sub> = 25Ω (Note 1, 2)		80	90	ns
Turn-On Rise Time	t <sub>R</sub>		89	100	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		125	160	ns	
Turn-Off Fall Time	t <sub>F</sub>		64	80	ns	
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 8A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				8	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				32	A

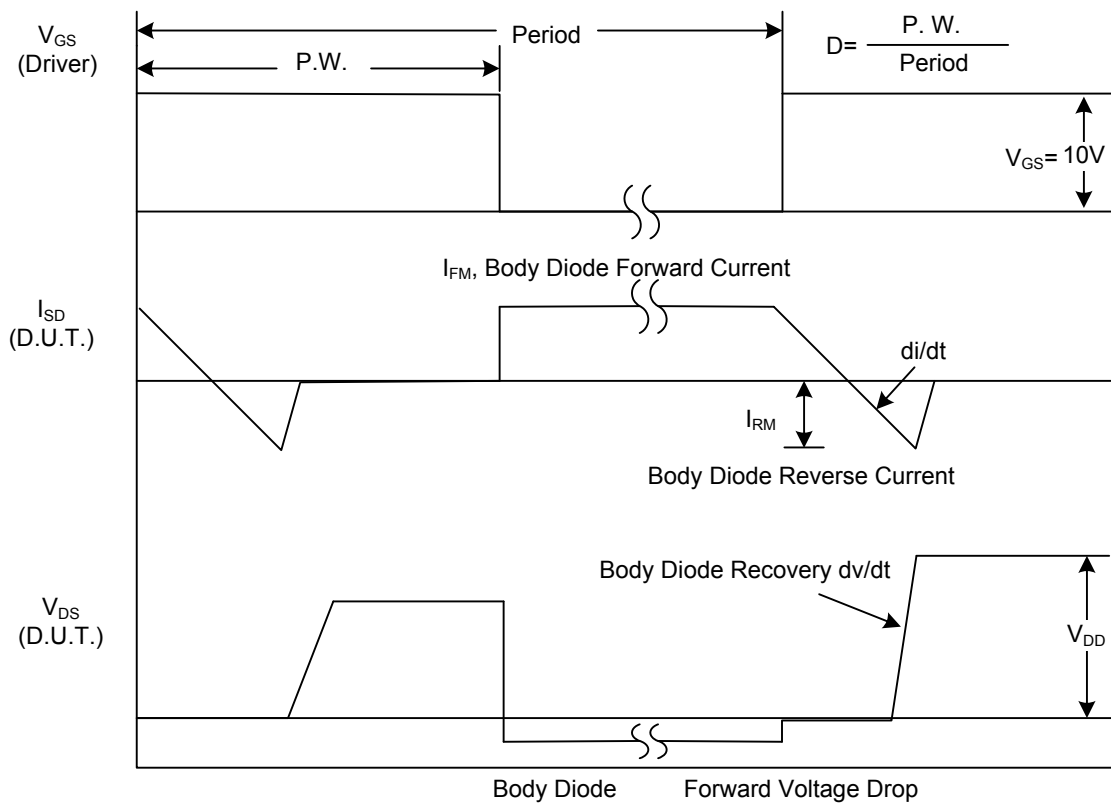
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

## TEST CIRCUITS AND WAVEFORMS

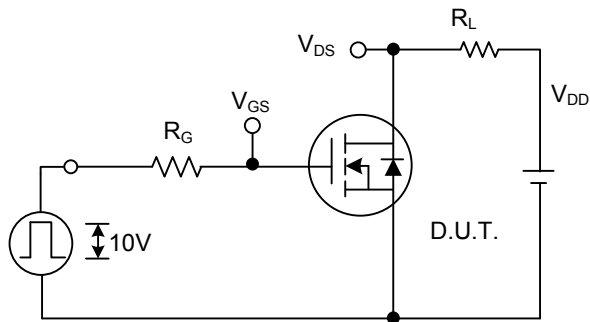


**Peak Diode Recovery dv/dt Test Circuit**

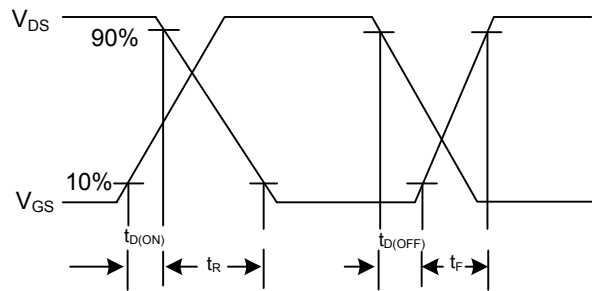


**Peak Diode Recovery dv/dt Waveforms**

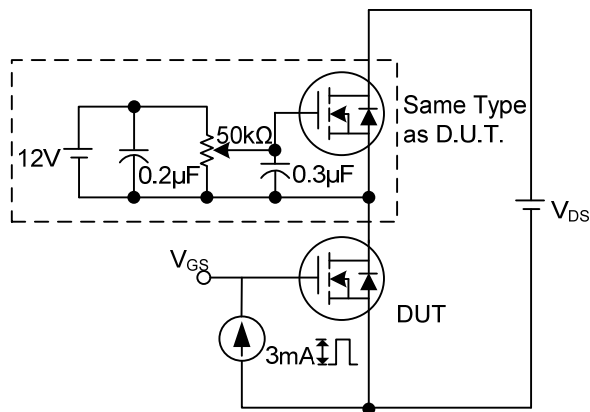
## ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



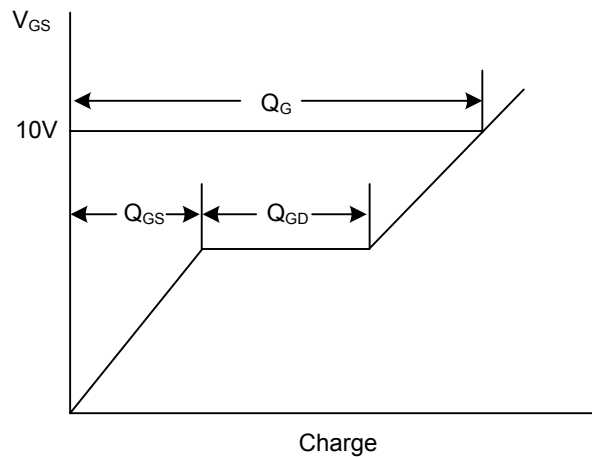
**Switching Test Circuit**



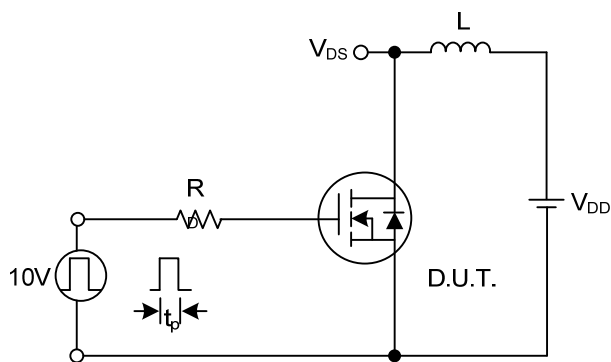
**Switching Waveforms**



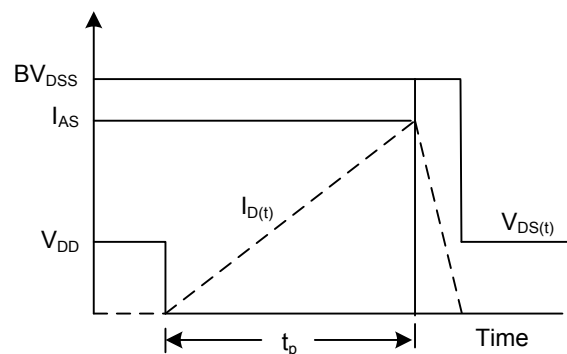
**Gate Charge Test Circuit**



**Gate Charge Waveform**



**Unclamped Inductive Switching Test Circuit**



**Unclamped Inductive Switching Waveforms**

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